

Amendments of the Claims

The following listing of claims will replace all prior versions, and listings, of claims in the above-identified patent application:

Listing of Claims

1-54. (cancelled)

55. (currently amended) A semiconductor comprising:

a semiconductor substrate having a downwardly extending cavity formed therein;

5 a first spiral conductor formed in the cavity, said first spiral conductor being fabricated substantially in a first horizontal plane within the cavity; and

10 a second spiral conductor formed in the cavity, said second spiral conductor being fabricated substantially in a second horizontal plane within the cavity and above the first plane, wherein the first and second spiral conductors are electrically isolated from one another and are positioned to be inductively coupled during operation.

56. (previously presented) The semiconductor of claim 55 wherein the first and second spiral conductors have an inductive coupling coefficient greater than about 0.8.

57. (currently amended) The semiconductor of claim 55 wherein:

each of said ~~inductors~~ conductors has a center; and

5 said centers are substantially aligned along an axis.

58. (previously presented) The semiconductor of claim 57 wherein:

said first inductor has a first number of turns; and

5 said second inductor has a second number of turns.

59. (previously presented) The semiconductor of claim 58 wherein said first and second numbers are equal.

60. (previously presented) The semiconductor of claim 59 wherein:

 said semiconductor has a major surface defining a plane; and

5 said cavity is formed in said major surface.

61. (previously presented) The semiconductor of claim 60 wherein said cavity comprises:

 a bottom surface substantially parallel to said plane; and

5 a side wall substantially perpendicular to said plane.

62. (withdrawn) The semiconductor of claim 60 wherein said cavity comprises:

 a bottom surface substantially parallel to said plane; and

5 a side wall at an oblique angle relative to said plane.

63. (withdrawn) The semiconductor of claim 62 wherein said side wall is at an angle of about 54.74° relative to said plane.

64. (previously presented) The semiconductor of claim 58 wherein:

 said semiconductor has a major surface defining a plane; and

5 said cavity is formed in said major surface.

65. (previously presented) The semiconductor of claim 64 wherein said cavity comprises:

 a bottom surface substantially parallel to said plane; and

5 a side wall substantially perpendicular to
said plane.

66. (withdrawn) The semiconductor of claim 64
wherein said cavity comprises:

 a bottom surface substantially parallel to
said plane; and

5 a side wall at an oblique angle relative to
said plane.

67. (withdrawn) The semiconductor of claim 66
wherein said side wall is at an angle of about 54.74°
relative to said plane.

68. (previously presented) The semiconductor of
claim 57 wherein:

 said semiconductor has a major surface
defining a plane; and

5 said cavity is formed in said major surface.

69. (previously presented) The semiconductor of
claim 68 wherein said cavity comprises:

 a bottom surface substantially parallel to
said plane; and

5 a side wall substantially perpendicular to
said plane.

70. (withdrawn) The semiconductor of claim 68
wherein said cavity comprises:

 a bottom surface substantially parallel to
said plane; and

5 a side wall at an oblique angle relative to
said plane.

71. (withdrawn) The semiconductor of claim 70
wherein said side wall is at an angle of about 54.74°
relative to said plane.

72-78. (cancelled)